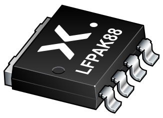

BUK7S1R2-80M

N-channel 80 V, 1.2 mOhm, Standard level MOSFET in LFPAK88

13 February 2024 **Preliminary data sheet**

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 14 low ohmic split-gate technology, for ultra-low R_{DSon} capability, housed in a LFPAK88 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 14 split-gate technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
  - Fast and efficient switching with optimal damping and low spiking
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joints
- LFPAK copper clip technology:
  - Improved reliability, with reduced R_{th}, R_{DSon} and package inductance
  - Increases maximum current capability and improved current spreading

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motor, lighting and solenoid control
- Ultra high-performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	80	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	-	335	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	341	W
T_j	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.7	1	1.2	mΩ

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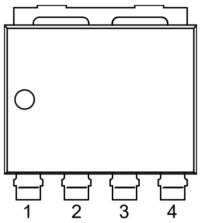
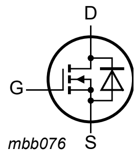
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V; Fig. 13; Fig. 14		82	164	246	nC

[1] 335 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 LFPAK88 (SOT1235)	
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7S1R2-80M	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7S1R2-80M	`7S1R280M`

8. Limiting values

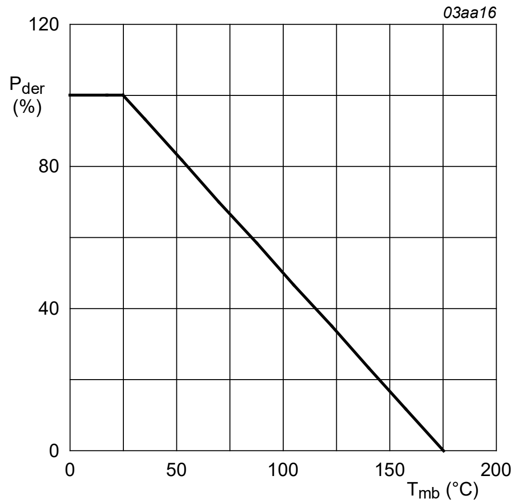
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	80	V
V_{GS}	gate-source voltage			-20	20	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	341	W
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	335	A
		V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 2		-	249	A
I_{DM}	peak drain current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C; Fig. 3		-	1406	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C

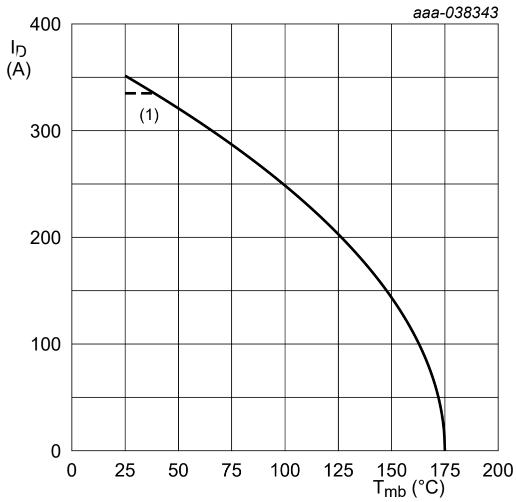
Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I_S	source current	T_{mb} = 25 °C		-	335	A
I_{SM}	peak source current	pulsed; $t_p \leq$ 10 µs; T_{mb} = 25 °C		-	1406	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 93 A; $V_{sup} \leq$ 80 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2] [3] [4]	-	867	mJ

[1] 335 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
[2] Protected by 100% test.
[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[4] Refer to application note AN10273 for further information.



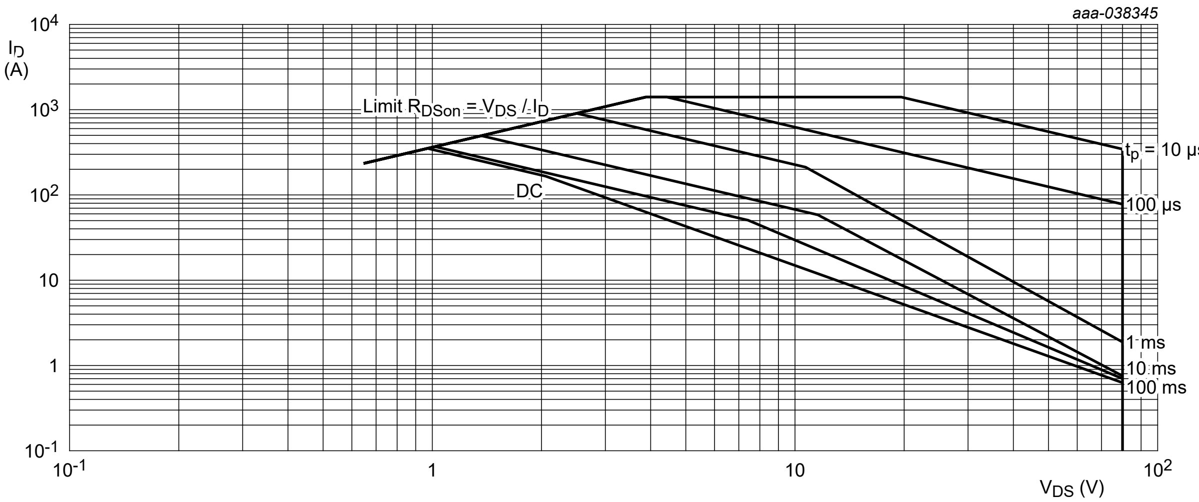
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature



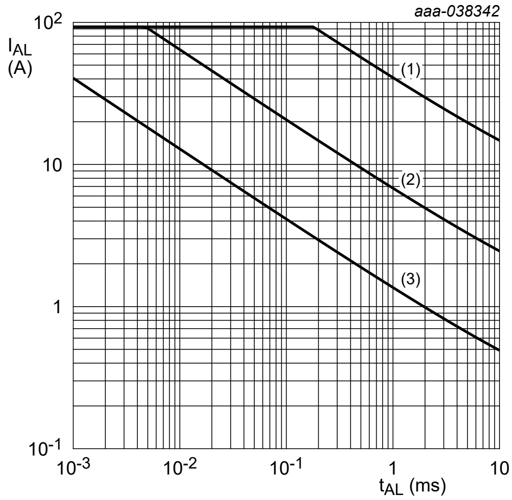
$V_{GS} \geq$ 10 V
(1) 335 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j\ (init)}$ = 25 °C; (2) $T_{j\ (init)}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	-	24	-	K/W

[1] Device on 4 layer PCB. Refer to TN00008 for further information.

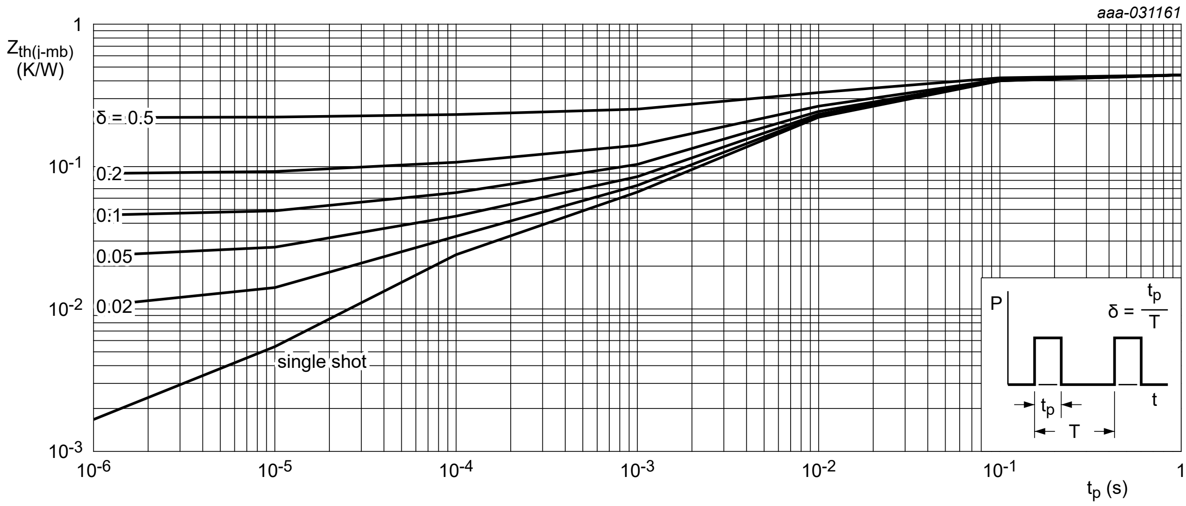
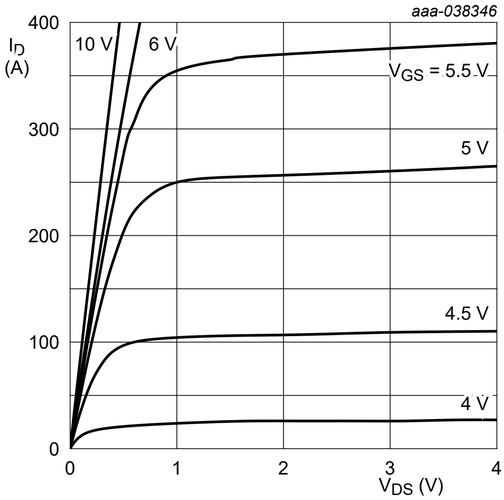


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

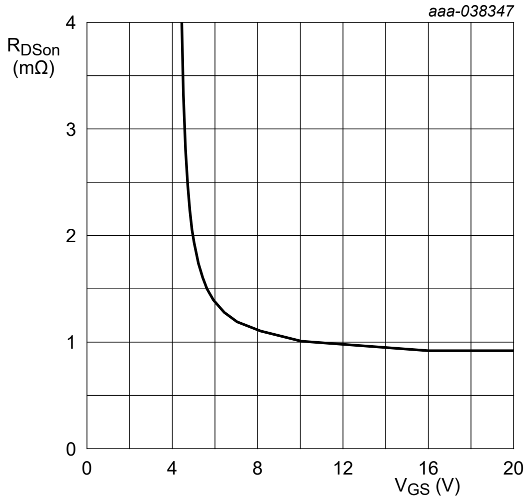
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		80	86	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -40 °C		-	84	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		72	83	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 °C; Fig. 9		2	3	4	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175 °C; Fig. 10		1	1.7	-	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55 °C; Fig. 10		-	3.4	4.6	V
I_{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C		-	0.03	1	µA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 125 °C		-	8	100	µA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C		-	0.13	1	mA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.7	1	1.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 105 °C; Fig. 12		1.2	1.6	2.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 125 °C; Fig. 12		1.3	1.8	2.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12		1.5	2.2	2.8	mΩ
R_G	gate resistance	f = 1 MHz; T_j = 25 °C		0.5	1	2	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V; Fig. 13; Fig. 14		82	164	246	nC
Q_{GS}	gate-source charge			18	46	74	nC
Q_{GD}	gate-drain charge			10	29	67	nC
C_{iss}	input capacitance	V_{DS} = 40 V; V_{GS} = 0 V; f = 0.5 MHz; Fig. 15		7134	11891	16647	pF
C_{oss}	output capacitance			1058	2645	4761	pF
C_{rss}	reverse transfer capacitance			19	97	253	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 40 V; R_L = 1.6 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	40	-	ns
t_r	rise time			-	34	-	ns
$t_{d(off)}$	turn-off delay time			-	104	-	ns
t_f	fall time			-	51	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.77	1	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 40 V; Fig. 17		-	57	-	ns
Q_r	recovered charge			-	68	-	nC



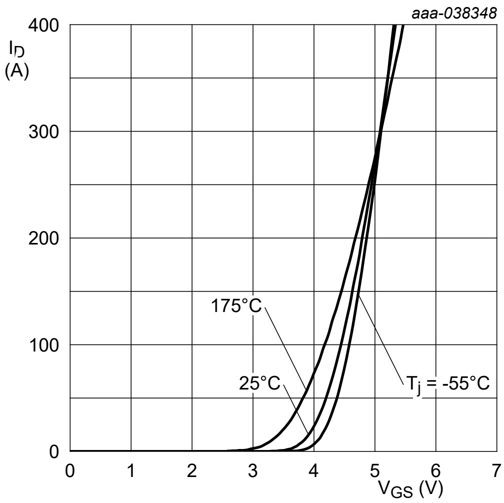
T_j = 25 °C

Fig. 6. **Output characteristics; drain current as a function of drain-source voltage; typical values**



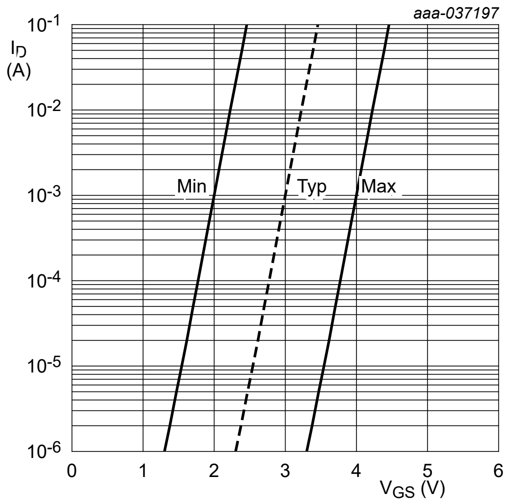
T_j = 25 °C; I_D = 25 A

Fig. 7. **Drain-source on-state resistance as a function of gate-source voltage; typical values**



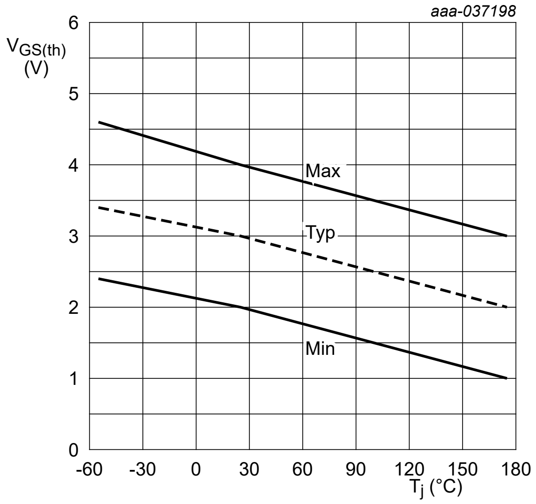
V_{DS} = 8 V

Fig. 8. **Transfer characteristics; drain current as a function of gate-source voltage; typical values**



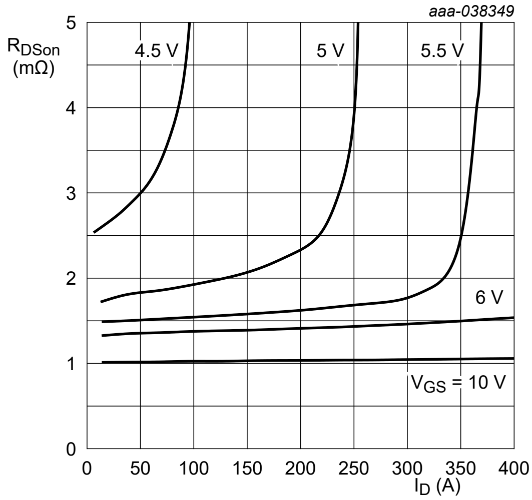
T_j = 25 °C; V_{DS} = 5 V

Fig. 9. **Sub-threshold drain current as a function of gate-source voltage**



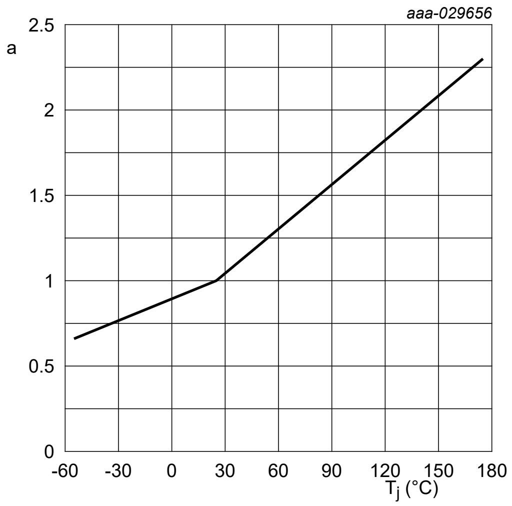
I_D = 1 mA ; V_{DS} = V_{GS}

Fig. 10. Gate-source threshold voltage as a function of junction temperature



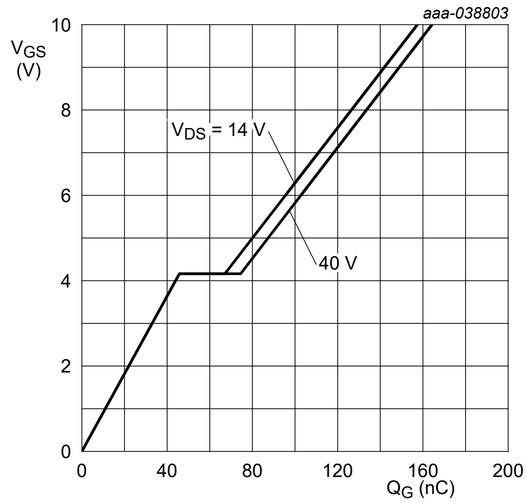
T_j = 25 °C

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon\ (25°C)}}$$

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature



T_j = 25 °C; I_D = 25 A

Fig. 13. Gate-source voltage as a function of gate charge; typical values

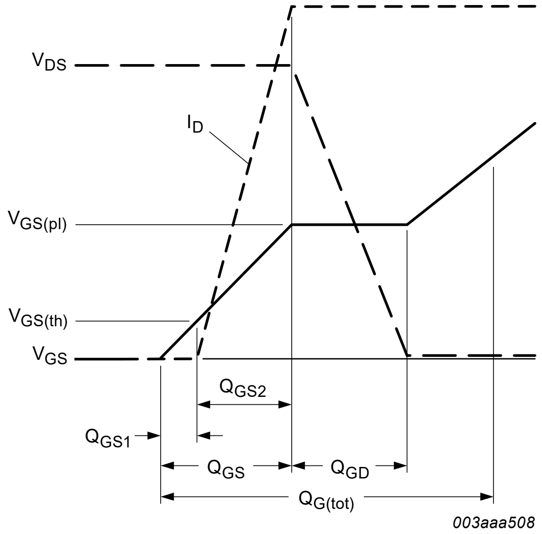
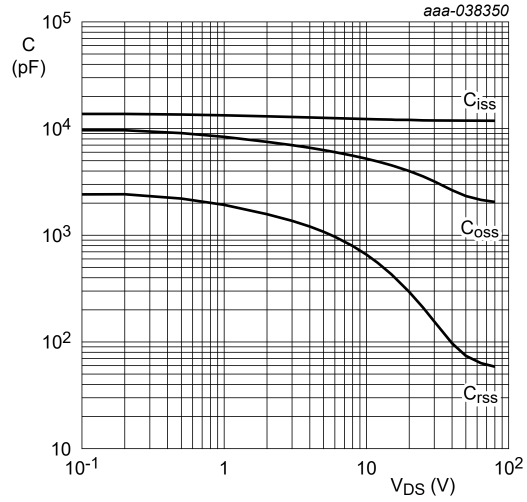
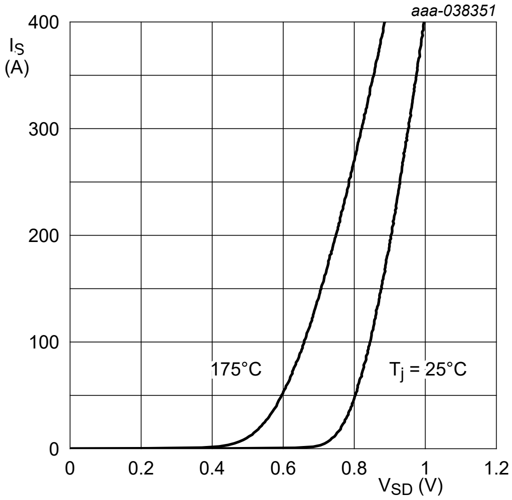


Fig. 14. Gate charge waveform definitions



V_{GS} = 0 V; f = 0.5 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{GS} = 0 V

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

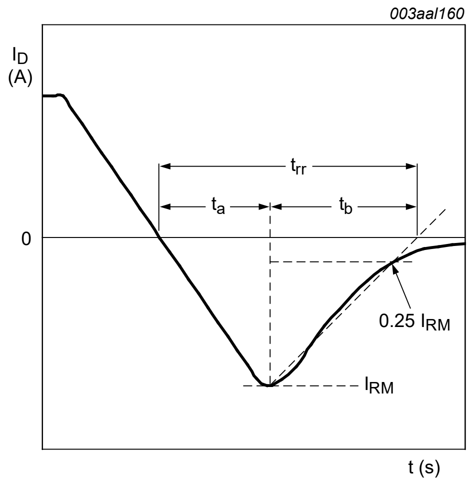
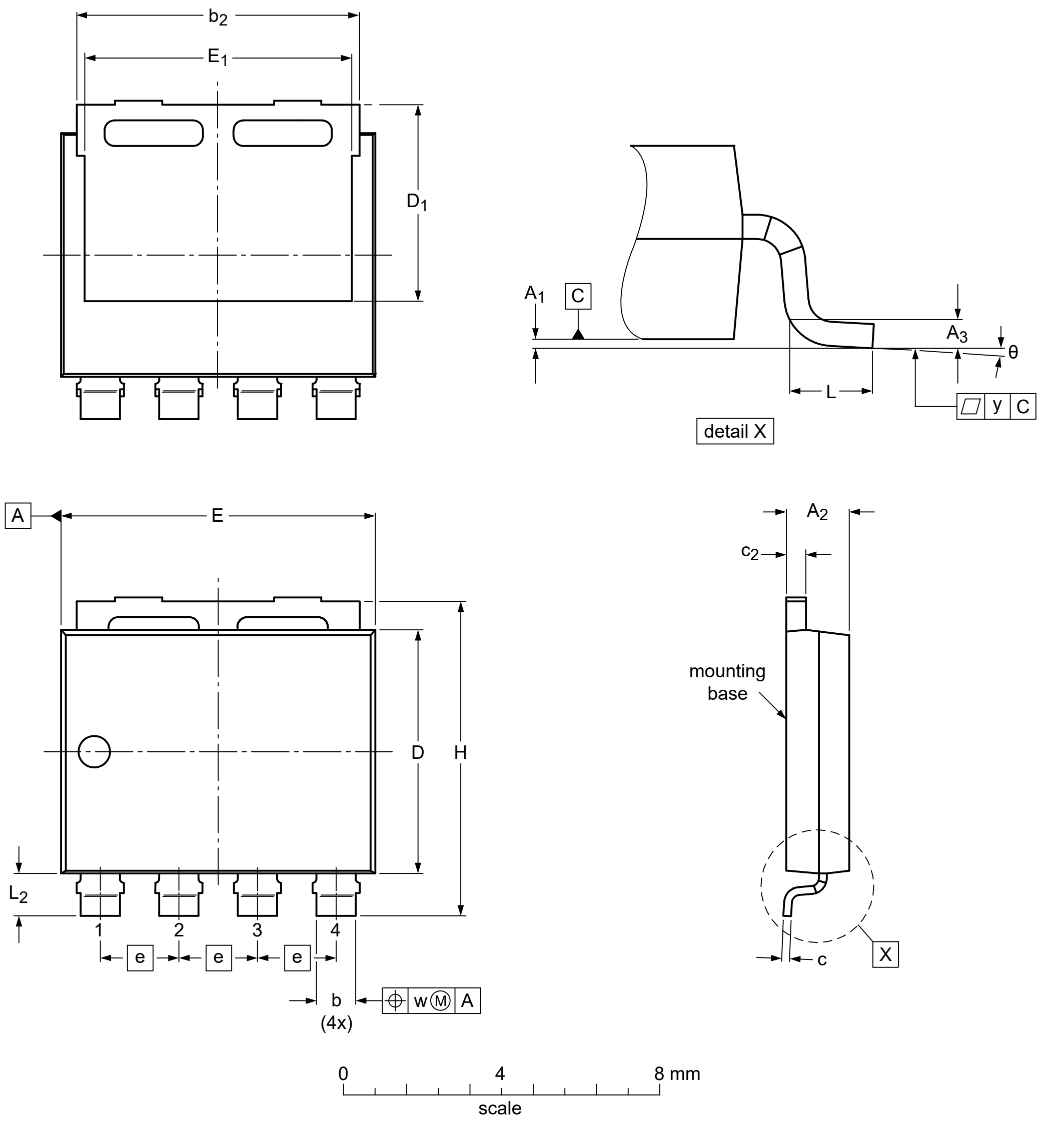


Fig. 17. Reverse recovery timing definition

11. Package outline

Plastic single-ended surface-mounted package (LFPAK88); 4 leads **SOT1235**



Dimensions (mm are the original dimensions)

Unit		A_1	A_2	A_3	b	b_2	c	c_2	D(1)	D_1(1)	E(1)	E_1(1)	e	H(1)	L	L_2	w	y	θ
mm	max	0.15	1.7		1.1	7.3	0.24	0.55	6.3	5.1	8.1	6.9		8.1	0.8	1.3			8°
	nom			0.25									2.0				0.25	0.10	
	min	0.00	1.5		0.9	7.1	0.18	0.45	6.1	4.9	7.9	6.7		7.8	0.6	0.9			0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot1235_po

Outline version	References: IEC	References: JEDEC	References: JEITA		European projection	Issue date
SOT1235						~~17-08-02~~ 17-08-07

Fig. 18. Package outline LFPAK88 (SOT1235)

12. Soldering

Footprint information for reflow soldering of LFPAK88 package **SOT1235**

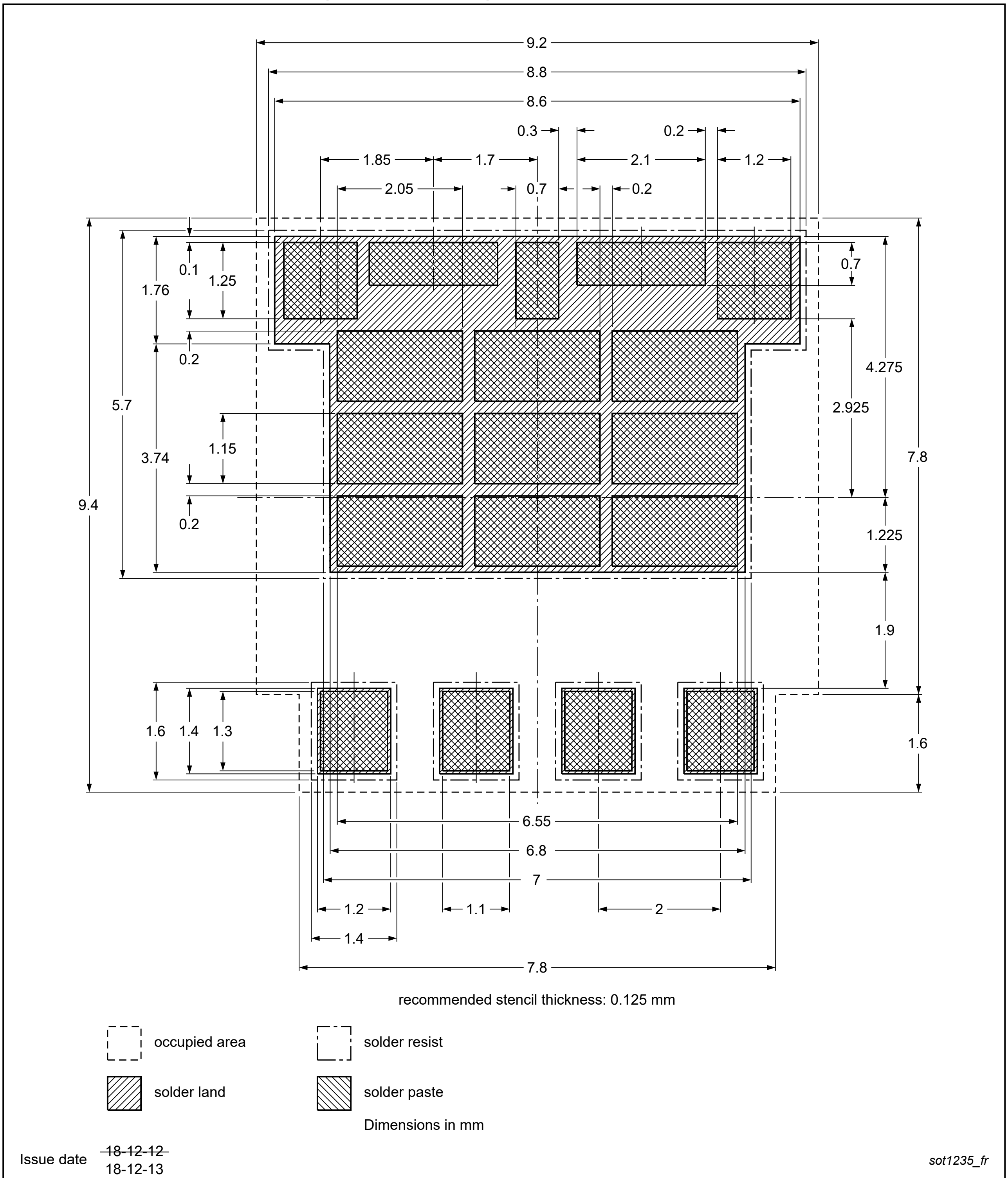


Fig. 19. Reflow soldering footprint for LFPAK88 (SOT1235)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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Contents

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Date of release: 13 February 2024